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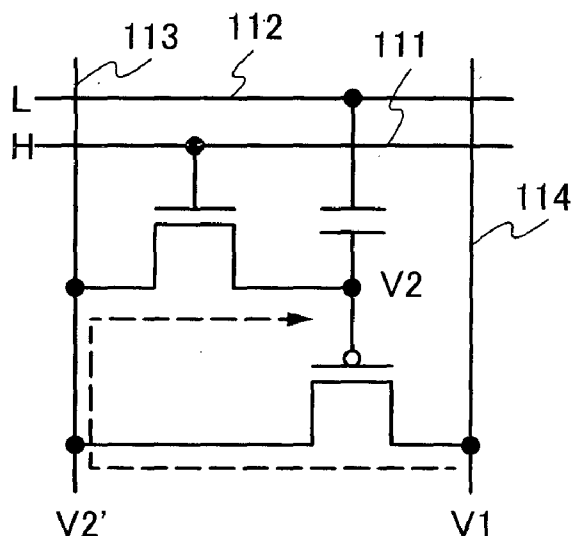
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(54) Title: SEMICONDUCTOR DEVICE AND METHOD FOR DRIVING SEMICONDUCTOR DEVICE

FIG. 3D



(57) Abstract: To provide a semiconductor device which can write and read a desired potential. The semiconductor device includes a first transistor (Tr), a second Tr, and a capacitor. In the semiconductor device, operation of writing data is performed by a first step and a second step. In the first step, a low voltage is applied to a bit line and a first wiring to turn on the first Tr and the second Tr. In the second step, a first voltage is applied to the first wiring, and application of the low voltage to the bit line is stopped. Operation of reading the data is performed by a third step and a fourth step. In the third step, a high voltage is applied to the first wiring. In the fourth step, application of the high voltage to the first wiring is stopped, and a low voltage is applied to a capacitor line.